A METHOD OF MANUFACTURING A LATERALLY DIFFUSED METAL OXIDE SEMICONDUCTOR DEVICE

ABSTRACT OF THE DISCLOSURE

A method of manufacturing a laterally diffused metal oxide semiconductor (LDMOS) device, and an integrated circuit associated therewith. The method includes forming a lightly-doped source/drain region with a first dopant, the lightly-doped source/drain region located between first and second isolation structures. The method further includes creating a gate over the lightly-doped source/drain region. In one advantageous embodiment of the present invention, the method further includes diffusing a second dopant at least partially across the lightly-doped source/drain region and under the gate to form a first portion of a channel.